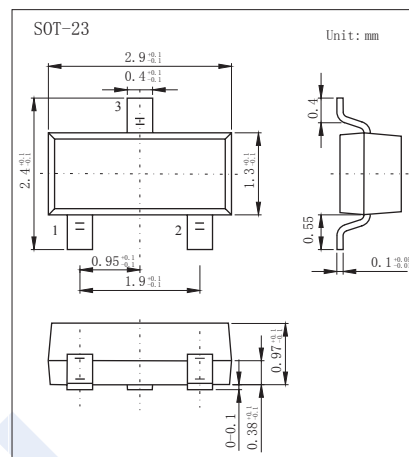
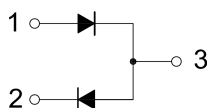


Switching Diodes

MMBD7000 (KMBD7000)

■ Features

- Dual Switching Diode
- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse Voltage	V _{RM}	100	V
Peak Repetitive Reverse Voltage	V _{RRM}	75	
Working Peak Reverse Voltage	V _{RWM}		
RMS Reverse Voltage	V _{RMS}	53	
Average Rectified Output Current	I _o	200	mA
Non-Repetitive Peak Forward Surge Current @ t = 1μs @ t = 1s	I _{FSM}	2	A
		1	
Power Dissipation	P _d	225	mW
Thermal Resistance Junction to Ambient	R θ JA	556	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100\text{ }\mu\text{A}$	100			V
Forward voltage	V_F	$I_F = 1\text{ mA}$			0.7	
		$I_F = 10\text{ mA}$			0.82	
		$I_F = 100\text{ mA}$			1.1	
Reverse voltage leakage current	I_R	$V_R = 50\text{ V}$			1	μA
		$V_R = 100\text{ V}$			3	
Diode capacitance	C_T	$V_R = 0\text{ V}, f = 1\text{ MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$			4	ns

■ Marking

Marking	5C
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Switching Diodes

MMBD7000 (KMBD7000)

■ Typical Characteristics

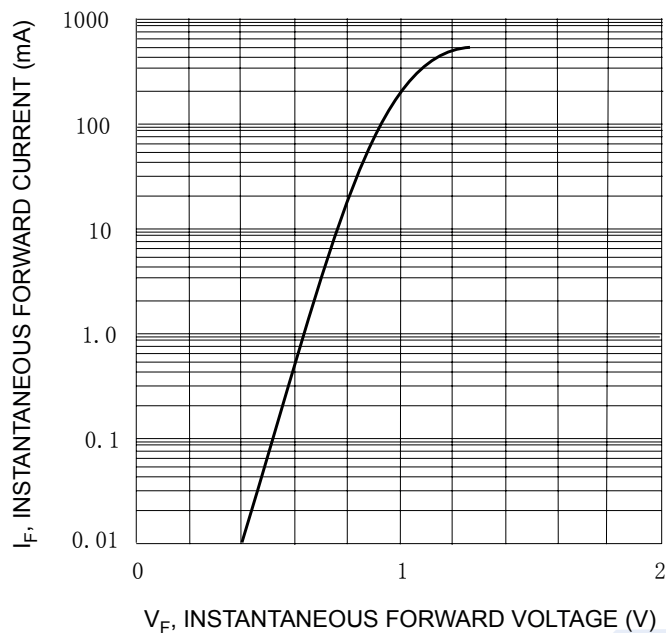


Fig. 1 Forward Characteristics

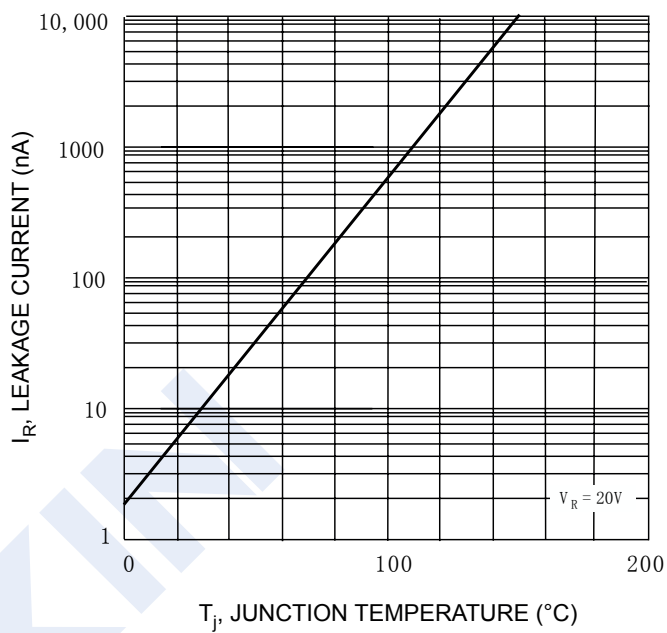


Fig. 2 Leakage Current vs Junction Temperature